# 2SA1550

## Silicon PNP triple diffusion planar type

### For power switching

### Features

- High foward current transfer ratio h<sub>FE</sub>
- High-speed switching
- ullet High collector to base voltage  $V_{CBO}$
- I type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

### Absolute Maximum Ratings (T<sub>C</sub>=25°C)

Parameter		Symbol	Ratings	Unit
Collector to base voltage		$V_{CBO}$	-400	V
Collector to emitter voltage		$V_{CEO}$	-400	V
Emitter to base voltage		$V_{\mathrm{EBO}}$	-7	V
Peak collector current		$I_{CP}$	-1.0	A
Collector current		$I_{C}$	- 0.5	A
Collector power	T <sub>C</sub> =25°C	D	15	-W
dissipation	Ta=25°C	$P_{C}$	1.3	W
Junction temperature		$T_j$	150	°C
Storage temperature		$T_{ m stg}$	-55 to +150	°C

# Unit: mm 3.5±0.2 1.1±0.1 0.85±0.1 0.4±0.1 2.3±0.2 4.6±0.4 1 2 3 1.Base 2.Collector 3:Emitter I Type Package Unit: mm 3.5±0.2 0.85±0.1 0.4±0.1 1.1±0.1 0.4±0.1 0

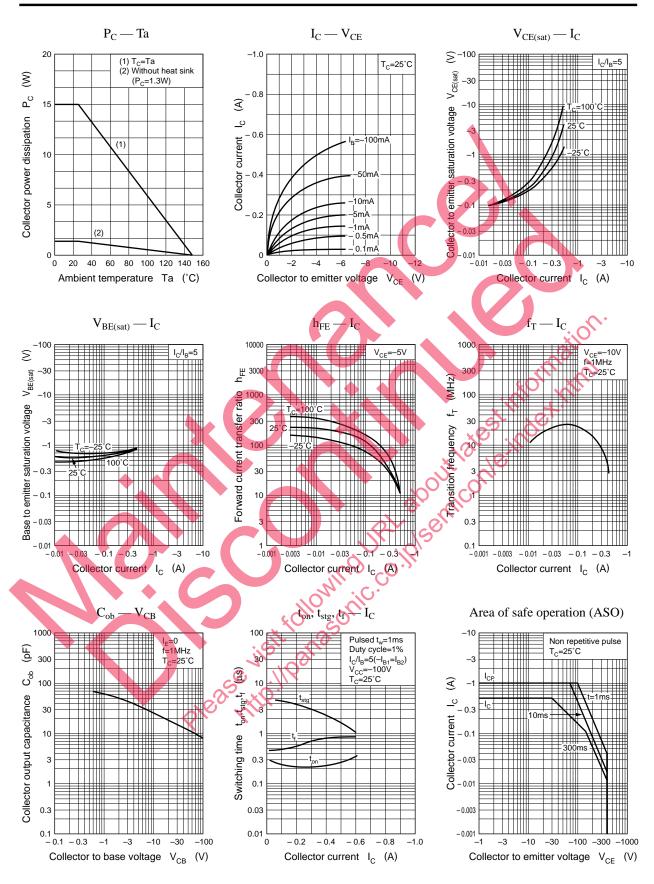
### Electrical Characteristics (T<sub>C</sub>=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -400V$ , $I_E = 0$			-100	μА
Emitter cutoff current	I <sub>EBO</sub>	$V_{BB} = 7V, I_C = 0$			-100	μА
Collector to emitter voltage	$V_{CEO}$	$I_{\rm C} = -10  {\rm mA}, I_{\rm B} = 0$	-400			V
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = -5V, I_{C} = -50 \text{mA}$	80		280	
	h <sub>FE2</sub>	$V_{CE} = -5V, I_{C} = -300 \text{mA}$	10			
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -200  \text{mA}, I_{\rm B} = -40  \text{mA}$			-1.5	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = -200 \text{mA}, I_B = -40 \text{mA}$			-1.5	V
Transition frequency	$f_T$	$V_{CE} = -10V, I_C = -100mA, f = 1MHz$		20		MHz
Turn-on time	t <sub>on</sub>	$I_{\rm C} = -300  {\rm mA},$		0.25		μs
Storage time	t <sub>stg</sub>	$I_{B1} = -60 \text{mA}, I_{B2} = 60 \text{mA},$		2.0		μs
Fall time	t <sub>f</sub>	$V_{CC} = -200V$		0.5		μs

### \*h<sub>FE1</sub> Rank classification

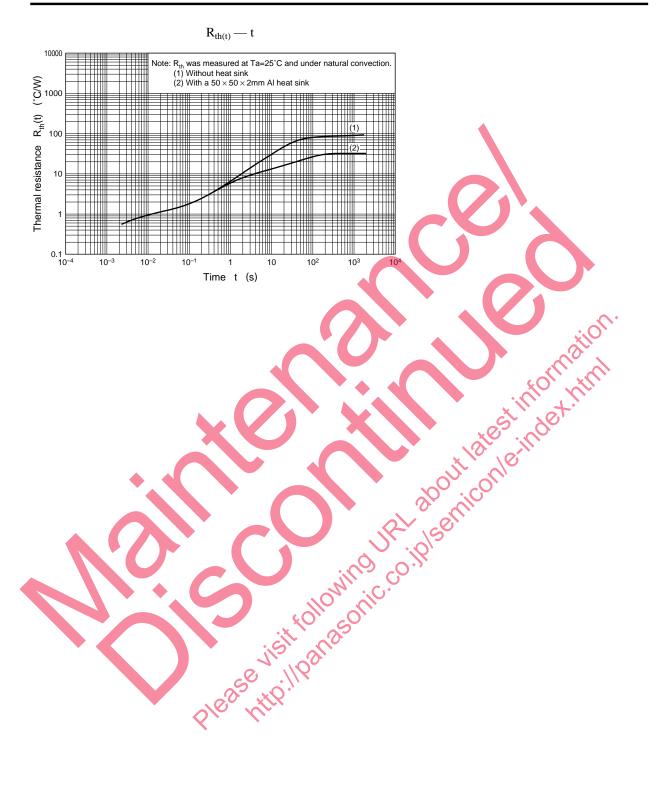
Rank	Q	P
h <sub>FE1</sub>	80 to 160	130 to 280

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